

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE6080AI uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

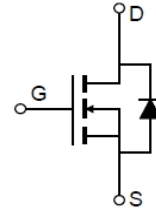
General Features

- $V_{DS} = 60V, I_D = 80A$
 $R_{DS(ON)} = 6.0m\Omega$ (typical) @ $V_{GS} = 10V$
 $R_{DS(ON)} = 7.0m\Omega$ (typical) @ $V_{GS} = 4.5V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- PWM
- Load Switching

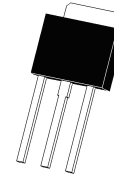
100% UIS TESTED!
100% ΔV_{ds} TESTED!



Schematic diagram



Marking and pin assignment



TO-251-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE6080AI	NCE6080AI	TO-251-3L	-	-	-

Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	80	A
Drain Current-Continuous($T_c = 100^\circ C$)	$I_D(100^\circ C)$	56.5	A
Pulsed Drain Current	I_{DM}	320	A
Maximum Power Dissipation	P_D	110	W
Derating factor		0.73	W/ $^\circ C$
Single pulse avalanche energy (Note 1)	E_{AS}	390	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.36	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	50	$^\circ C/W$

Electrical Characteristics (T_c=25°C unless otherwise noted)

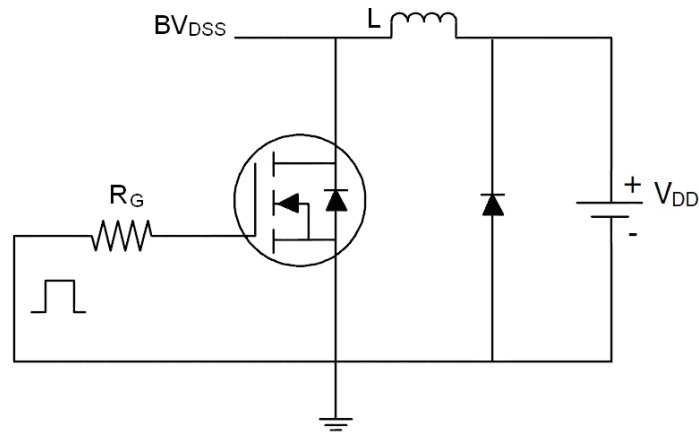
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.8	1.3	1.8	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	6.0	7.5	mΩ
		V _{GS} =4.5V, I _D =20A	-	7.0	9.0	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =20A	20	-	-	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, F=1.0MHz	-	4000	-	pF
Output Capacitance	C _{oss}		-	290	-	pF
Reverse Transfer Capacitance	C _{rss}		-	210	-	pF
Switching Characteristics (Note 3)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, R _L =1Ω V _{GS} =10V, R _G =3Ω	-	8.5	-	nS
Turn-on Rise Time	t _r		-	7	-	nS
Turn-Off Delay Time	t _{d(off)}		-	40	-	nS
Turn-Off Fall Time	t _f		-	15	-	nS
Total Gate Charge	Q _g	V _{DS} =30V, I _D =20A, V _{GS} =10V	-	90.3	-	nC
Gate-Source Charge	Q _{gs}		-	10.9	-	nC
Gate-Drain Charge	Q _{gd}		-	20.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =20A	-	-	1.2	V
Diode Forward Current	I _S		-	-	80	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 20A di/dt = 100A/μs	-	32	-	nS
Reverse Recovery Charge	Q _{rr}		-	45	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

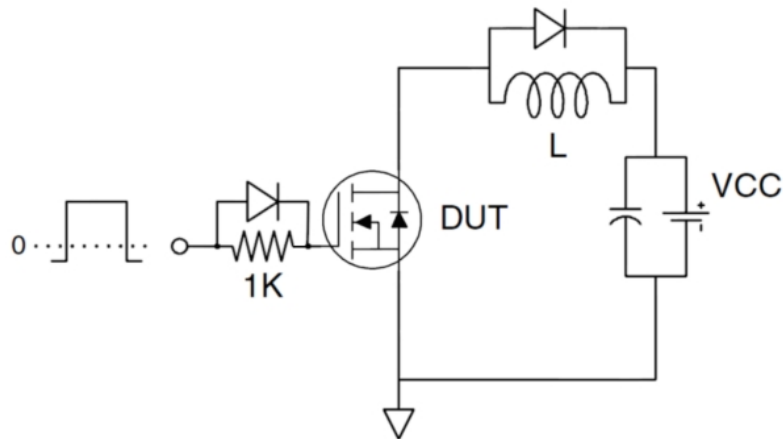
- EAS condition : T_j=25°C, V_{DD}=30V, V_G=10V, L=0.5mH, R_G=25Ω.
- The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The maximum allowed junction temperature of 175°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.
- Guaranteed by design, not subject to production.
- These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175°C. The SOA curve provides a single pulse rating.

Test circuit

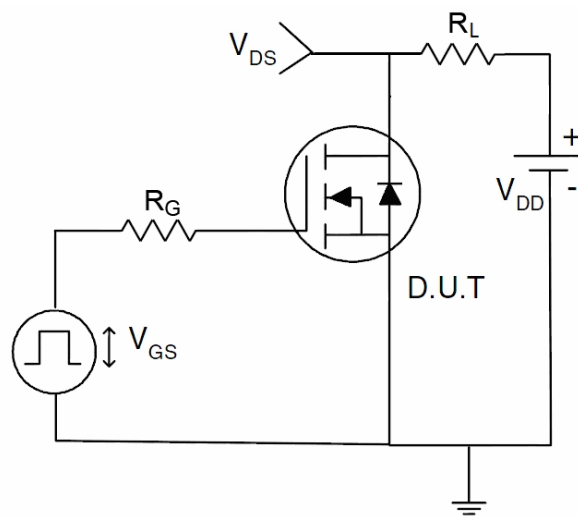
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

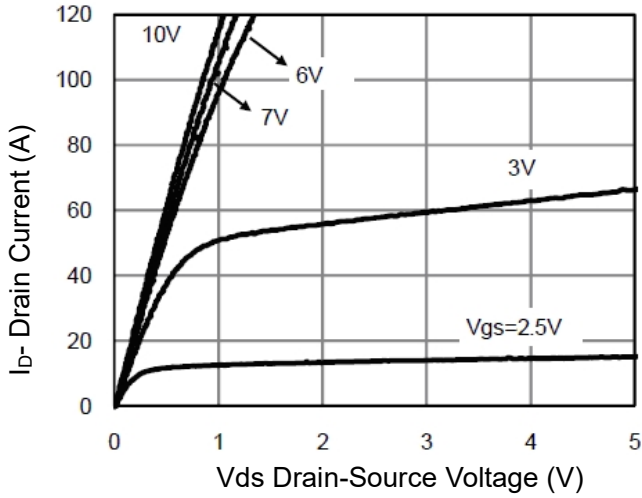


Figure 1 Output Characteristics

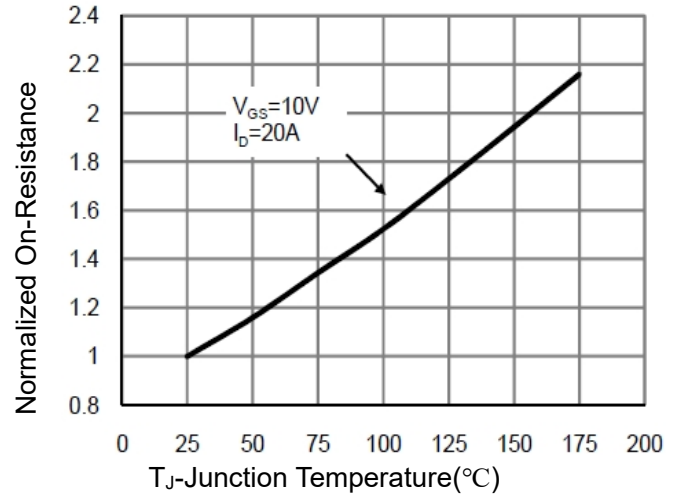


Figure 4 Rdson-Junction Temperature

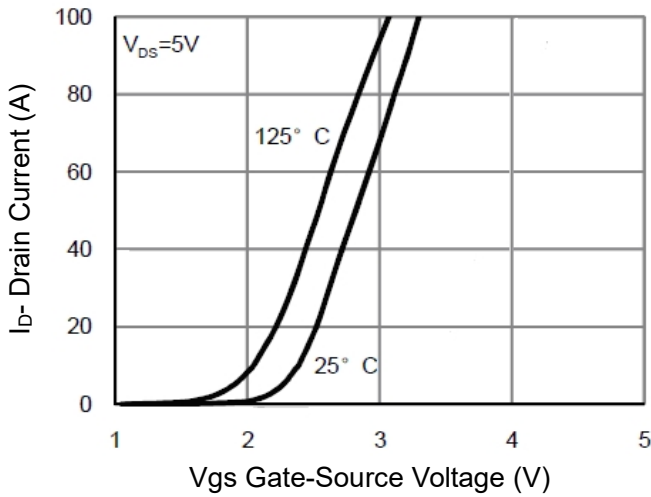


Figure 2 Transfer Characteristics

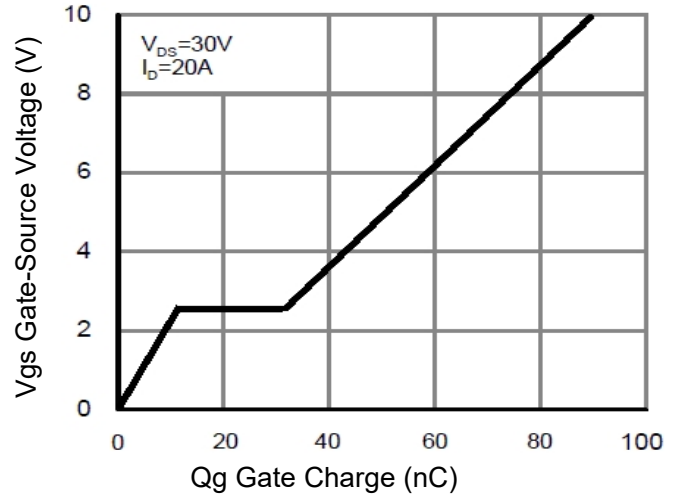


Figure 5 Gate Charge

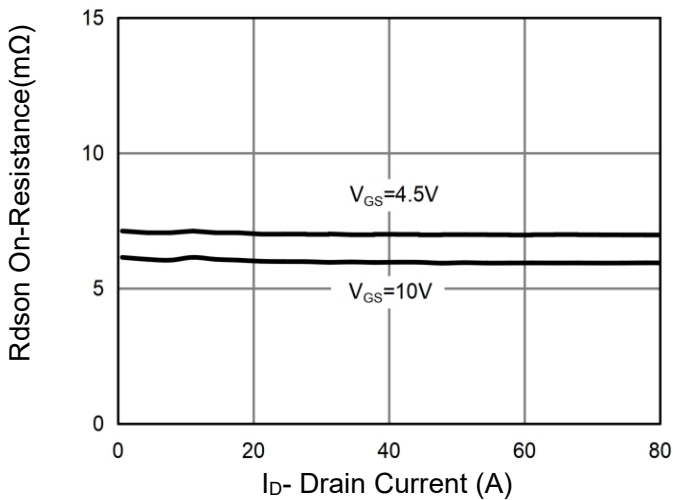


Figure 3 Rdson- Drain Current

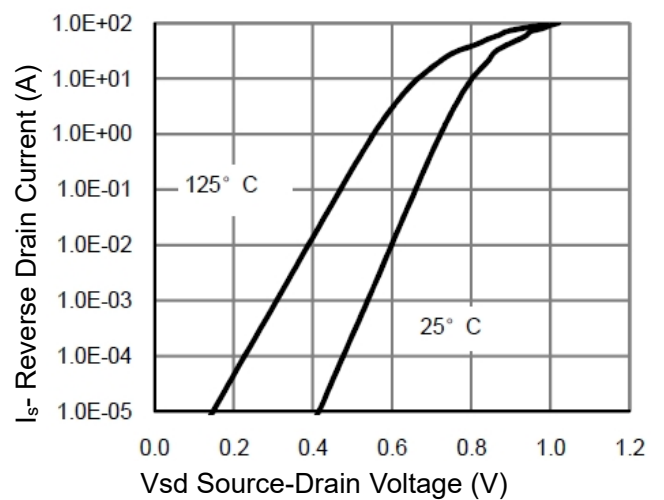


Figure 6 Source- Drain Diode Forward

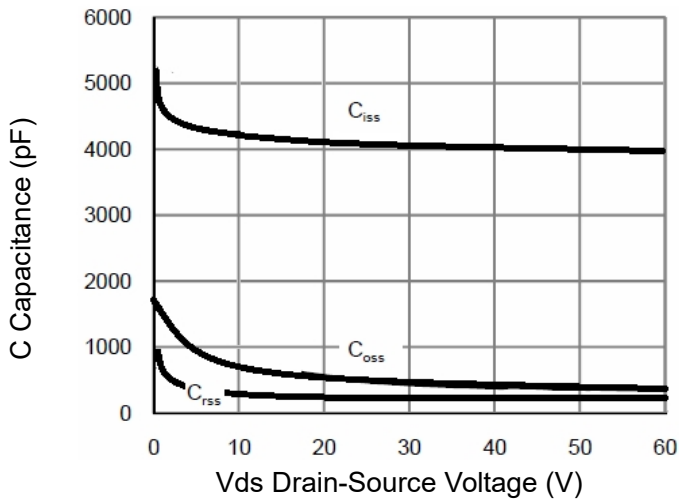


Figure 7 Capacitance vs Vds

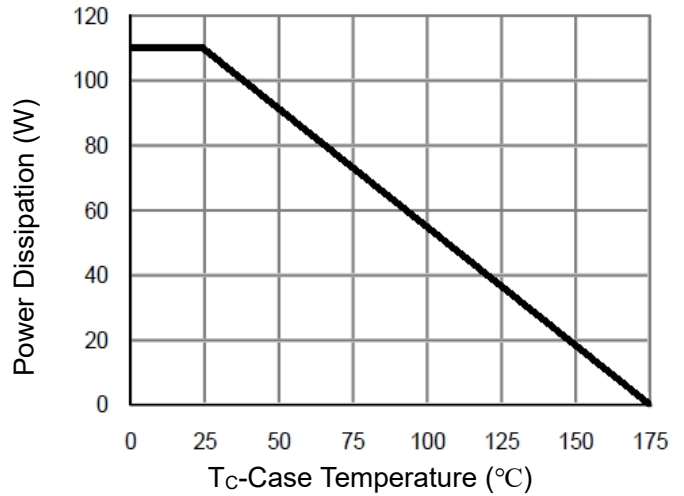


Figure 9 Power De-rating

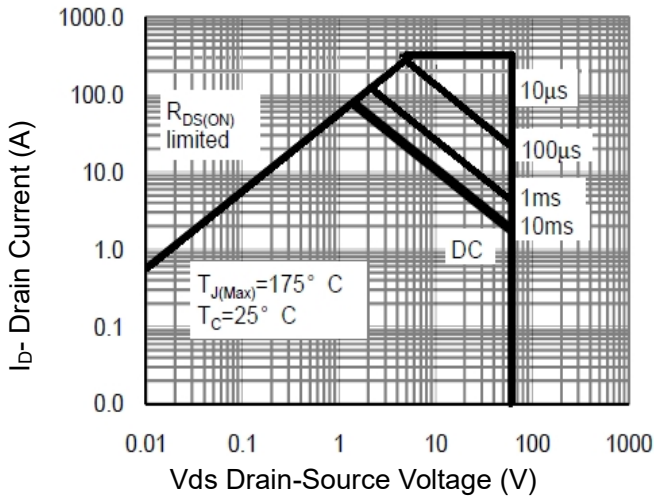


Figure 8 Safe Operation Area (Note 4)

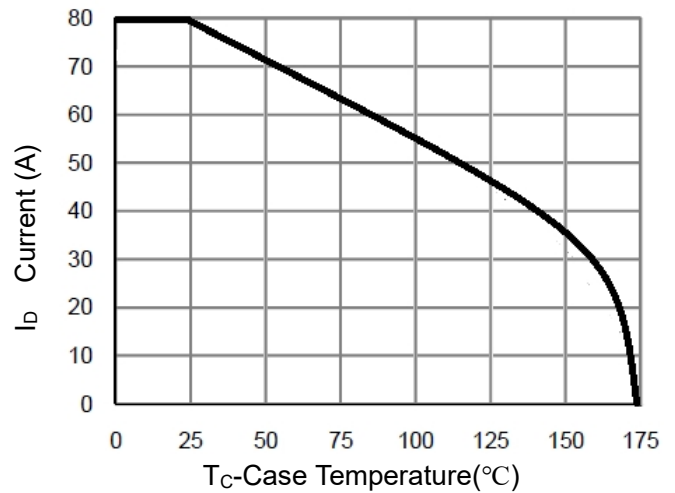


Figure 10 Drain Current De-rating

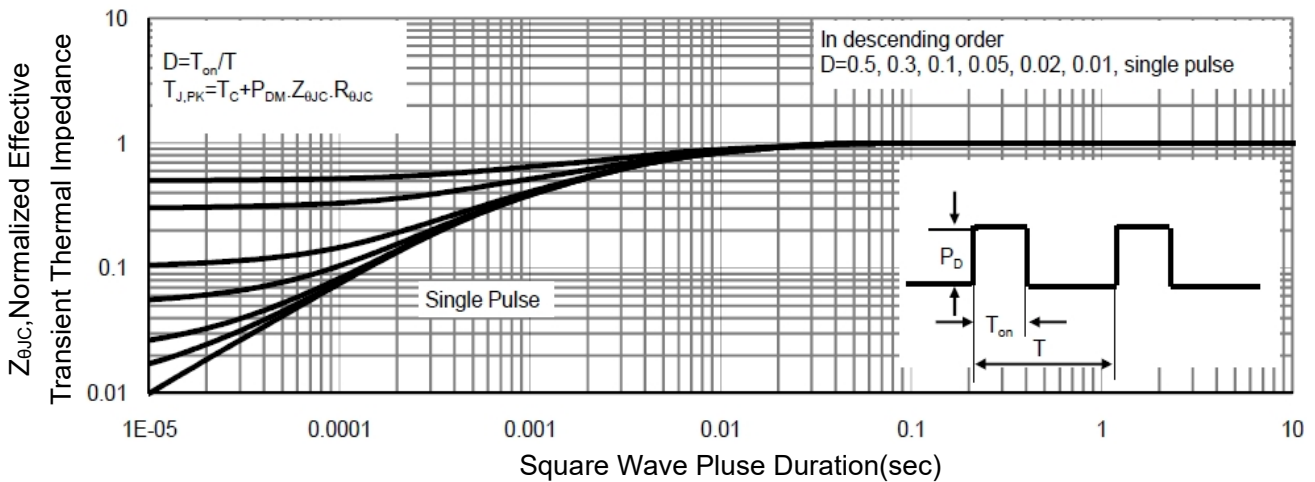
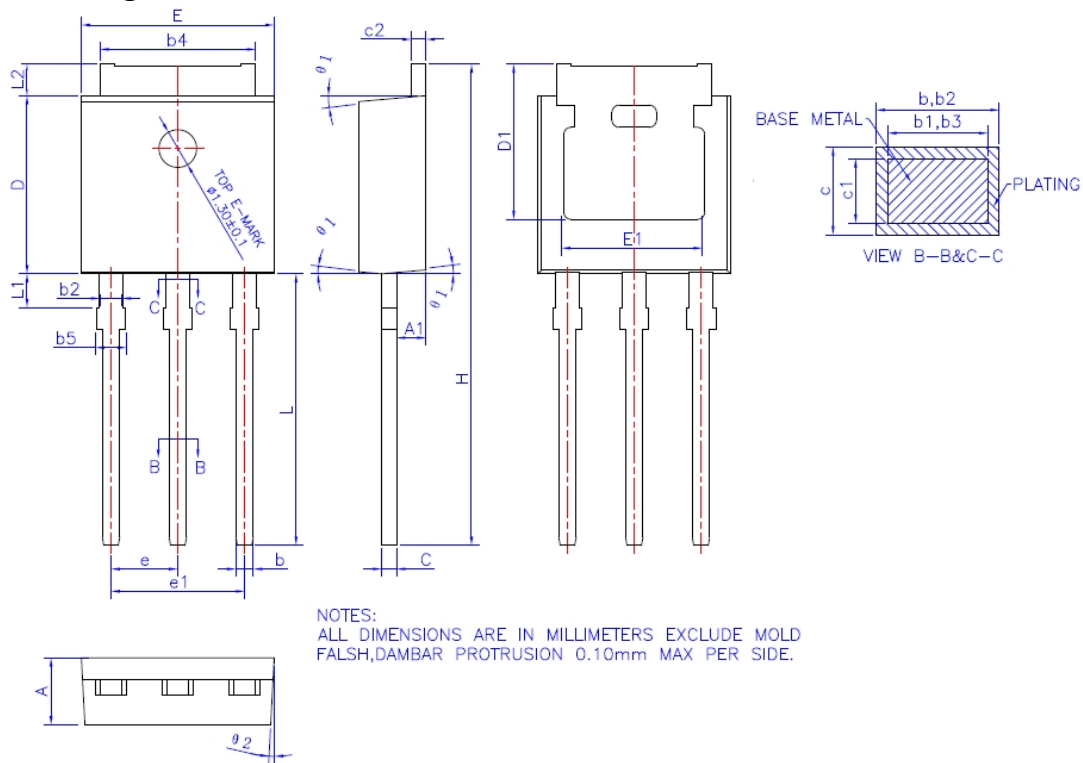


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-251-3L Package Information



NOTES:
ALL DIMENSIONS ARE IN MILLIMETERS EXCLUDE MOLD
FLASH,DAMBAR PROTRUSION 0.10mm MAX PER SIDE.

COMMON DIMENSIONS (UNITS OF MEASURE =MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	2.20	2.30	2.35
A1	0.90	1.01	1.10
b	0.56	---	0.69
b1	0.55	0.60	0.65
b2	0.77	---	0.90
b3	0.76	0.81	0.86
b4	5.23	5.33	5.43
b5	---	---	1.05
c	0.46	---	0.59
c1	0.45	0.51	0.55
c2	0.46	---	0.59
D	6.00	6.10	6.20
D1	5.20	---	---
E	6.50	6.60	6.70
E1	4.60	4.83	5.00
e	2.24	2.29	2.34
e1	4.47	4.57	4.67
H	16.18	16.48	16.78
L	9.00	9.30	9.60
L1	0.95	1.16	1.35
L2	0.90	1.08	1.25
θ1	3°	5°	7°
θ2	1°	3°	5°

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